

MC74LVX132

Product Preview

Quad 2-Input NAND Schmitt Trigger

The MC74LVX132 is an advanced high speed CMOS Schmitt NAND trigger fabricated with silicon gate CMOS technology.

Pin configuration and function are the same as the MC74LVX00, but the inputs have hysteresis.

The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

- High Speed: $t_{PD} = 5.8\text{ns}$ (Typ) at $V_{CC} = 3.3\text{V}$
- Low Power Dissipation: $I_{CC} = 2\mu\text{A}$ (Max) at $T_A = 25^\circ\text{C}$
- Power Down Protection Provided on Inputs
- Low Noise: $V_{OLP} = 0.5\text{V}$ (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V

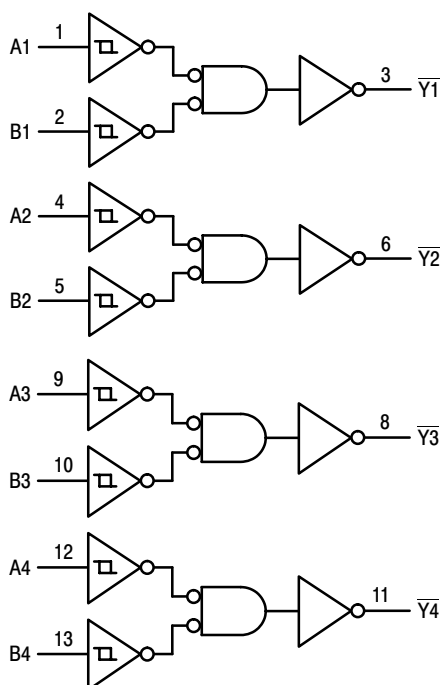


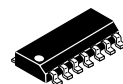
Figure 1. Logic Diagram

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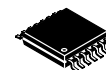


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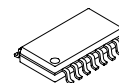
<http://onsemi.com>



14-LEAD SOIC
D SUFFIX
CASE 751A



14-LEAD TSSOP
DT SUFFIX
CASE 948G



14-LEAD SOIC EIAJ
M SUFFIX
CASE 965

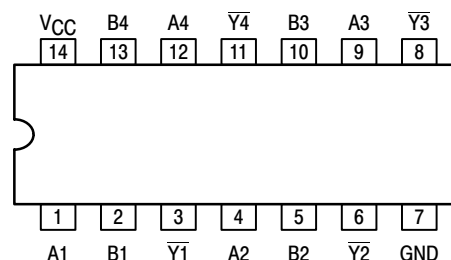


Figure 2. Pin Connection and Marking Diagram (Top View)

For detailed package marking information, see the Marking Diagram section on page 350 of this data sheet.

ORDERING INFORMATION

Device	Package	Shipping
MC74LVX132D	SOIC	55 Units/Rail
MC74LVX132DT	TSSOP	96 Units/Rail
MC74LVX132M	SOIC EIAJ	50 Units/Rail

FUNCTION TABLE

A Input	B Input	$\bar{Y}$ Output
L	L	H
L	H	H
H	L	H
H	H	L

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MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	− 0.5 to + 7.0	V
V _{IN}	DC Input Voltage	− 0.5 to + 7.0	V
V _{OUT}	DC Output Voltage	− 0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current V _I < GND	− 20	mA
I _{OK}	DC Output Diode Current V _O < GND	± 20	mA
I _{OUT}	DC Output Sink Current	± 25	mA
I _{CC}	DC Supply Current per Supply Pin	± 50	mA
T _{STG}	Storage Temperature Range	− 65 to + 150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
T _J	Junction Temperature under Bias	+ 150	°C
θ _{JA}	Thermal Resistance SOIC TSSOP	250	°C/W
P _D	Power Dissipation in Still Air at 85°C SOIC TSSOP	250	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 30% – 35%	UL–94–VO (0.125 in)	
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 1.) Machine Model (Note 2.) Charged Device Model (Note 3.)	> 2000 > 200 N/A	V
I _{Latch-Up}	Latch-Up Performance Above V _{CC} and Below GND at 85°C (Note 4.)	± 300	mA

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute–maximum–rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

1. Tested to EIA/JESD22–A114–A.
2. Tested to EIA/JESD22–A115–A.
3. Tested to JESD22–C101–A.
4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Supply Voltage	2.0	3.6	V
V _I	Input Voltage (Note 5.)	0	5.5	V
V _O	Output Voltage (HIGH or LOW State)	0	5.5	V
T _A	Operating Free–Air Temperature	− 40	+ 125	°C
Δt/ΔV	Input Transition Rise or Fall Rate V _{CC} = 3.0 V ± 0.3 V	0	100	ns/V

5. Unused inputs may not be left open. All inputs must be tied to a high– or low–logic input voltage level.

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DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} V	T _A = 25°C			T _A = ≤ 85°C		T _A = ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{T+}	Positive Threshold Voltage (5)		2.0 3.0 3.6	1.15 1.50 1.70	1.31 1.82 2.12	1.60 2.25 2.60	1.15 1.50 1.70	1.60 2.25 2.60	1.15 1.50 1.70	1.60 2.25 2.60	V
V _{T−}	Negative Threshold Voltage (5)		2.0 3.0 3.6	0.30 0.75 1.00	0.64 1.13 1.46	0.9 1.45 1.90	0.30 0.75 1.00	0.90 1.45 1.90	0.30 0.75 1.00	0.90 1.45 1.90	V
V _H	Hysteresis Voltage (5)		2.0 3.0 3.6	0.30 0.30 0.35	0.70 0.76 0.69	1.30 1.50 1.60	0.30 0.30 0.35	1.30 1.50 1.60	0.30 0.30 0.35	1.30 1.50 1.60	V
V _{OH}	Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	I _{OH} = − 50μA I _{OH} = − 50μA I _{OH} = − 4mA	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		1.9 2.9 2.34		V
V _{OL}	Maximum Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50μA I _{OL} = 50μA I _{OL} = 4mA	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44		0.1 0.1 0.52	V
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5V or GND	3.6			± 0.1		± 1.0		± 1.0	μA
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	3.6			2.0		20		20	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0ns)

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A = ≤ 85°C		T _A = ≤ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A or B to $\bar{Y}$	V _{CC} = 2.7V C _L = 15pF C _L = 50pF		7.0 10.0	11.0 16.0	1.0 1.0	13.0 18.7	1.0 1.0	15.0 20.0	ns
		V _{CC} = 3.3 ± 0.3V C _L = 15pF C _L = 50pF		5.8 8.3	10.6 15.4	1.0 1.0	12.5 17.5	1.0 1.0	14.5 19.5	
t _{OSHL} , t _{OSLH}	Output to Output Skew (Note 6.)	V _{CC} = 2.7V C _L = 50pF			1.5		1.5		1.5	ns
		V _{CC} = 3.3 ± 0.3V C _L = 50pF			1.5		1.5		1.5	
C _{in}	Maximum Input Capacitance			4	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (Note 6.)	Typical @ 25°C, V _{CC} = 5.0 V								pF
		11								

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per gate). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input t_r = t_f = 3.0ns, C_L = 50pF, V_{CC} = 5.0 V)

Symbol	Characteristic	T _A = 25°C		Unit
		Typ	Max	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.5	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	−0.3	−0.5	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

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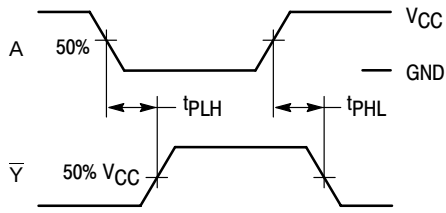
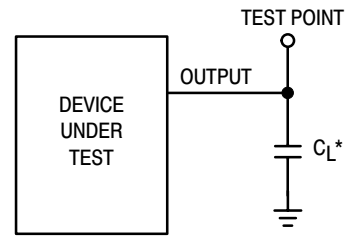


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

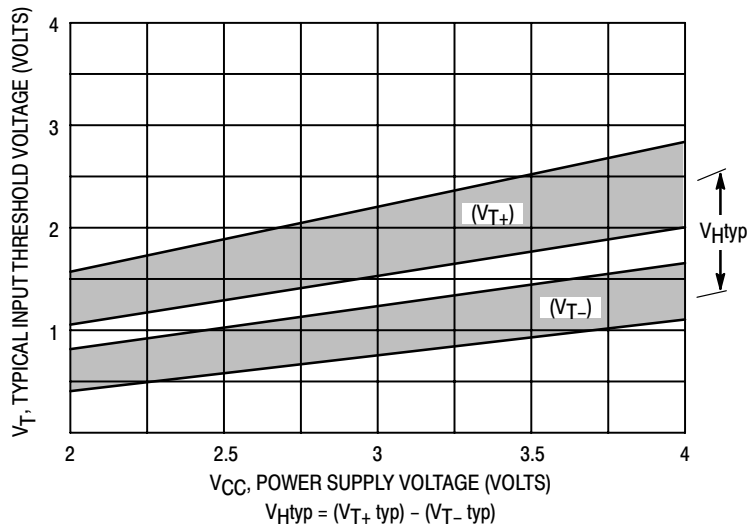


Figure 5. Typical Input Threshold, V_{T+} , V_{T-} versus Power Supply Voltage

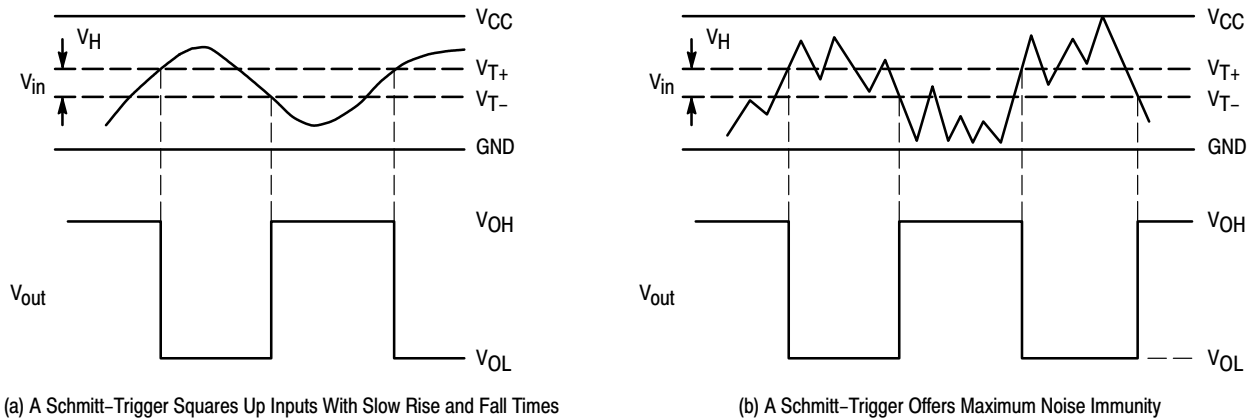


Figure 6. Typical Schmitt-Trigger Applications

MC74LVX132

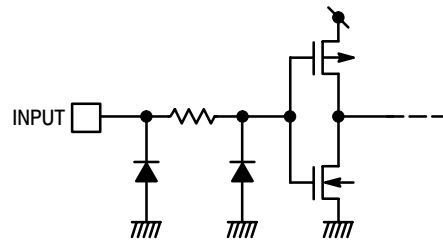
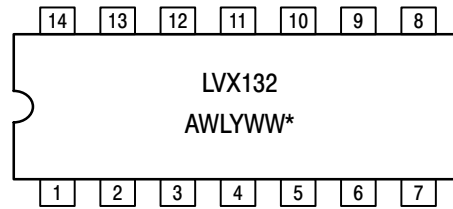
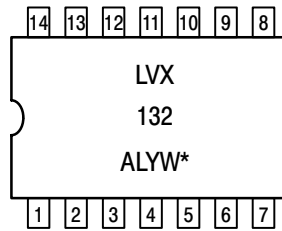


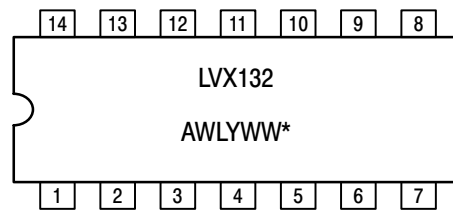
Figure 7. Input Equivalent Circuit



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14-LEAD SOIC EIAJ
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*See Applications Note #AND8004/D for date code and traceability information.

Figure 8. Marking Diagrams
(Top View)